

Phase Control Thyristors

Type: KP100A/600V

Features

- All diffused design
- High current capabilities
- High surge current capabilities
- High rates voltages
- High dV/dt
- Low gate current
- Dynamic gate
- Low thermal impedance
- Compact size and small weight

Typical Applications

- High Power Drives
- DC Motor Control
- High Voltage Power Supplies
- Medium power switching
- DC power supplies

Maximum Ratings And Characteristics

Symbol	Parameter		Values	Units	Test Conditions
ON-STATE					
I_{TAV}	Mean on-state current		-	A	Sinewave, 180° conduction, $T_c=100^\circ\text{C}$
I_{TRMS}	RMS value of on-state current		100	A	Nominal value
I_{TSM}	Peak one cycle surge (non repetitive) current		900	A	10.0 msec (50Hz), sinusoidal wave-shape, 180° conduction, $T_j = 125^\circ\text{C}$
I^2t	I square t		4050	A^2s	8.3 msec and 10.0 msec
I_L	Latching current		100	mA	$V_D = 12\text{ V}$; $R_L = 12\text{ ohms}$
I_H	Holding current		30	mA	$V_D = 12\text{ V}$; $I = 1\text{ A}$
V_{TM}	Peak on-state voltage		2.0	V	$I_{TM} = 150\text{ A}$; Duty cycle $\leq 0.01\%$; $T_j = 25^\circ\text{C}$
di/dt	Critical rate of rise of on-state current	non-repetitive	300	$A/\mu s$	Gate drive 20V, 20Ω, $t_r \leq 1\mu s$, $T_j = T_{jmax}$, anode voltage $\leq 80\% V_{DRM}$
		repetitive	50		
BLOCKING					
V_{DRM}	Repetitive peak off state voltage		600	V	
V_{RRM}	Repetitive peak reverse voltage				
V_{DSM}	Non repetitive peak off state voltage		700	V	
V_{RSM}	Non repetitive peak reverse voltage				
I_{DRM}	Repetitive peak off state current		10	mA	$T_j = 125^\circ\text{C}$, V_{RRM} , V_{DRM} applied
I_{RRM}	Repetitive peak reverse current				
dV/dt	Critical rate of voltage rise		100	$V/\mu s$	$T_j = T_{jmax}$, linear to 80% rated V_{DRM}
TRIGGERING					
$P_{G(AV)}$	Average gate power dissipation		-	W	
P_{GM}	Peak gate power dissipation		-	W	
I_{GM}	Peak gate current		-	A	
I_{GT}	Gate trigger current		200	mA	$T_c = 25^\circ\text{C}$
V_{GT}	Gate trigger voltage		3.0	V	$T_c = 25^\circ\text{C}$
$V_{T(T0)}$	Threshold voltage		1	V	
r_T	Slope resistance		2.4	$m\Omega$	
V_{GD}	Gate non-trigger voltage		0.2	V	$T_j = 125^\circ\text{C}$
SWITCHING					
t_q	Turn-off time		-	μs	$T_j = 125^\circ\text{C}$

t_d	Delay time	-	Gate current 1A, di/dt=1A/ μ s, $V_d=0.67\%V_{DRM}$, $T_J=25^\circ\text{C}$
Q_{rr}	Reverse recovery charge	-	

Thermal And Mechanical

Symbol	Parameter	Values	Units	Test Conditions
T_j	Operating temperature	-40~125	$^\circ\text{C}$	
T_{stg}	Storage temperature	-40~150	$^\circ\text{C}$	
$R_{th(j-c)}$	Thermal resistance - junction to case	0.4	$^\circ\text{C/W}$	DC operation , Single sided cooled
$R_{th(c-s)}$	Thermal resistance - case to sink	0.08	$^\circ\text{C/W}$	Single sided cooled
P	Mounting force	-	Nm	
W	Weight	-	g	about

OUTLINE

DIMENSIONS in millimeters (inches)

